Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

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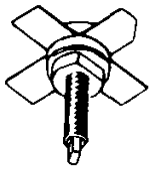
Microsemi
POWER PRODUCTS GROUP

MS1202

RF & MICROWAVE TRANSISTORS
FM MOBILE APPLICATIONS

Features

- 175 MHz
- 12.5 VOLTS
- P_{OUT} = 7.0 W
- G_P = 8.4 dB MINIMUM
- COMMON EMITTER CONFIGURATION

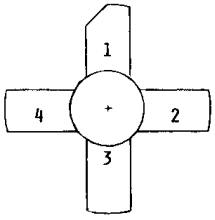


.380 4LSTUD (M135)
epoxy sealed

DESCRIPTION:

The MS1202 is a epitaxial silicon NPN transistor designed for 12.5 volt class C applications in the 118 – 136 MHz frequency band and 28 volt FM ground station applications. Gold metalization and emitter ballast resistors provide long term product ruggedness and reliability.

PIN CONNECTION



1 collector
2 emitter
3 base
4 emitter

ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector - Base Voltage	65	V
V_{CEO}	Collector - Emitter Voltage	35	V
V_{EBO}	Emitter - Base Voltage	4.0	V
P_{DISS}	Device Dissipation	15	W
T_J	Junction Temperature	200	°C
I_C	Device Current	1.0	A
T_{STG}	Storage Temperature	-65 to +200	°C

Thermal Data

$R_{TH(J-C)}$	Thermal Resistance Junction-case	11.7	°C/W

Rev A January 2009

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{ces}	I_C = 200 mA	V_{BE} = 0 mA	65	---	---	V
BV_{ceo}	I_C = 200 mA	I_B =0	35	---	---	V
BV_{ebo}	I_E = 5 mA	I_C = 0 mA	4	---	---	V
I_{cbo}	V_{CB} = 30 V	I_E = 0 mA	---	---	1.0	mA
H_{FE}	V_{CE} = 5 V	I_C = 100 mA	5	---	150	---

DYNAMIC

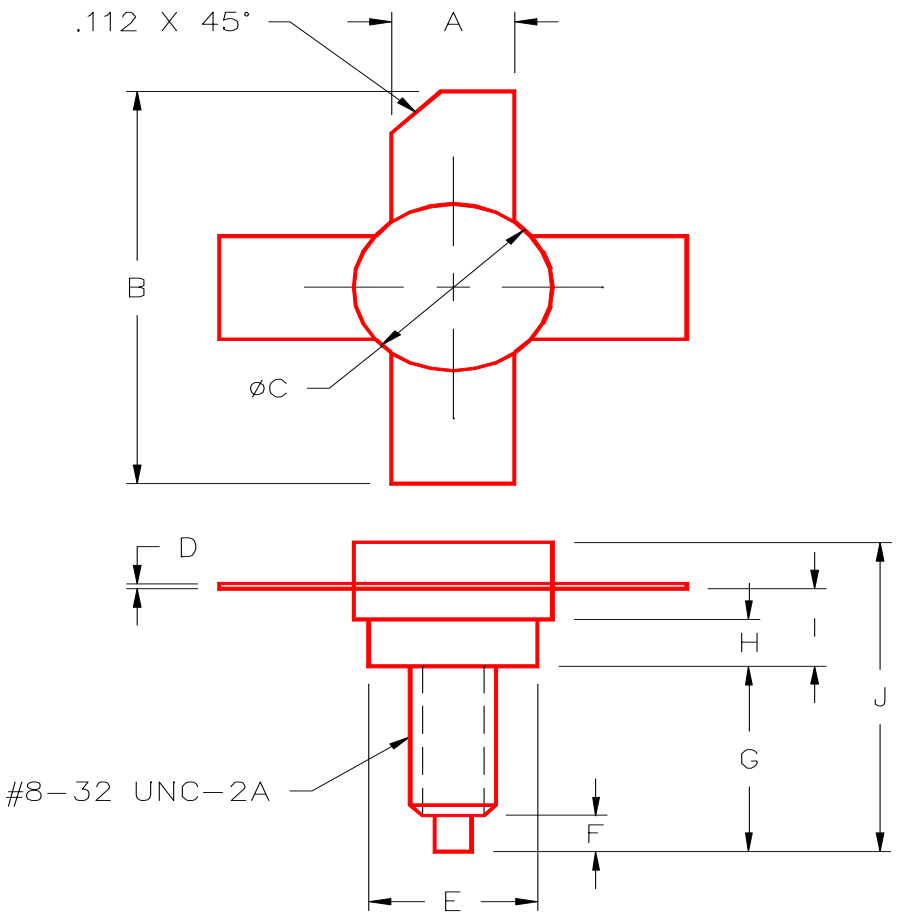
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
P_{OUT}	f =175 MHz	V_{CE} =28V	7.0	---	---	W
G_P	f =175 MHz	V_{CE} =28V	8.4	---	---	dB
η_c	f =175 MHz	V_{CE} =28V	60			%
Cob	f =1 MHz	V_{CE} =30V	---	---	15	pF

Microsemi
POWER PRODUCTS GROUP

MS1202

PACKAGE MECHANICAL DATA

PACKAGE STYLE M135



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.220/5,59	.230/5,84	I	.155/3,94	.175/4,45
B	.980/24,89		J		.750/19,05
C	.370/9,40	.385/9,78			
D	.004/0,10	.007/0,18			
E	.320/8,13	.330/8,38			
F	.100/2,54	.130/3,30			
G	.450/11,43	.490/12,45			
H	.090/2,29	.100/2,54			